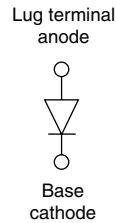


Schottky Rectifier, 120 A


HALF-PAK (D-67)


FEATURES

- 150 °C T_J operation
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS
COMPLIANT**

DESCRIPTION

The 120NQ.. high current Schottky rectifier module series has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

PRODUCT SUMMARY

$I_{F(AV)}$	120 A
V_R	45 V

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{F(AV)}$	Rectangular waveform	120	A
V_{RRM}		45	V
I_{FSM}	$t_p = 5 \mu s$ sine	26 000	A
V_F	120 Apk, $T_J = 125 \text{ }^\circ\text{C}$	0.62	V
T_J	Range	- 55 to 150	$^\circ\text{C}$

VOLTAGE RATINGS

PARAMETER	SYMBOL	120NQ045PbF	UNITS
Maximum DC reverse voltage	V_R	45	V
Maximum working peak reverse voltage	V_{RWM}		

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current See fig. 5	$I_{F(AV)}$	50 % duty cycle at $T_C = 105 \text{ }^\circ\text{C}$, rectangular waveform	120	A
Maximum peak one cycle non-repetitive surge current See fig. 7	I_{FSM}	5 μs sine or 3 μs rect. pulse	26 000	
		10 ms sine or 6 ms rect. pulse	1550	
Non-repetitive avalanche energy	E_{AS}	$T_J = 25 \text{ }^\circ\text{C}$, $I_{AS} = 13 \text{ A}$, $L = 1 \text{ mH}$	81	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum $V_A = 1.5 \times V_R$ typical	13	A

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop See fig. 1	$V_{FM}^{(1)}$	120 A	$T_J = 25\text{ }^\circ\text{C}$	0.63	V
		240 A		0.86	
		120 A	$T_J = 125\text{ }^\circ\text{C}$	0.62	
		240 A		0.81	
Maximum reverse leakage current See fig. 2	$I_{RM}^{(1)}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{Rated } V_R$	10	mA
		$T_J = 125\text{ }^\circ\text{C}$		500	
Maximum junction capacitance	C_T	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz) $25\text{ }^\circ\text{C}$		5200	pF
Typical series inductance	L_S	From top of terminal hole to mounting plane		7.0	nH
Maximum voltage rate of change	dV/dt	Rated V_R		10 000	V/ μs

Note(1) Pulse width < 500 μs

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum junction and storage temperature range	T_J, T_{Stg}			- 55 to 150	$^\circ\text{C}$
Maximum thermal resistance, junction to case	R_{thJC}	DC operation See fig. 4		0.38	$^\circ\text{C/W}$
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased		0.05	
Approximate weight				30	g
				1.06	oz.
Mounting torque	minimum	Non-lubricated threads		3 (26.5)	N · m (lbf · in)
	maximum			4 (35.4)	
Terminal torque	minimum			3.4 (30)	
	maximum			5 (44.2)	
Case style				HALF-PAK module	

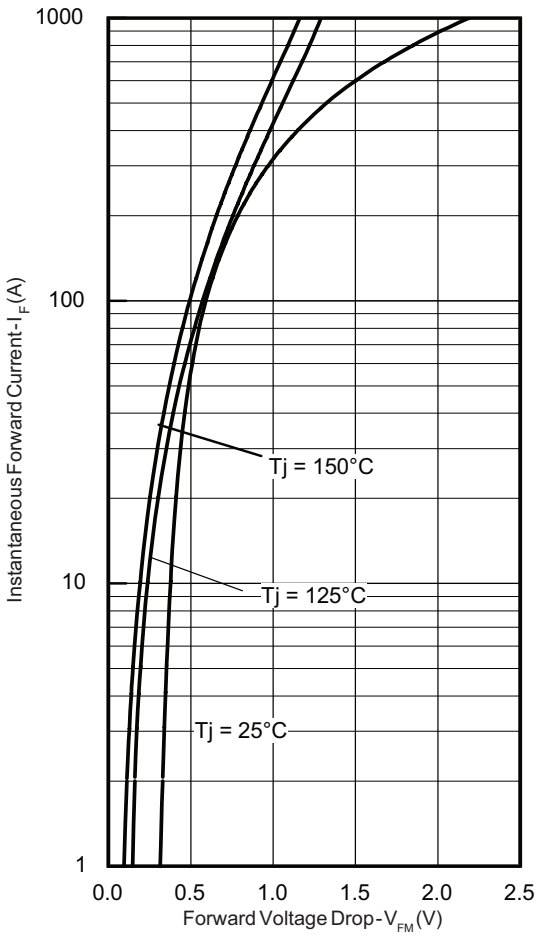


Fig. 1 - Maximum Forward Voltage Drop Characteristics

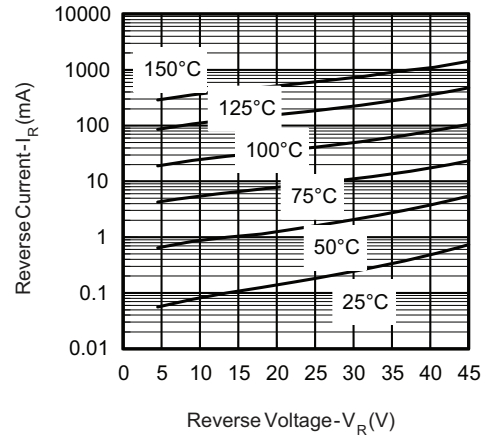


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

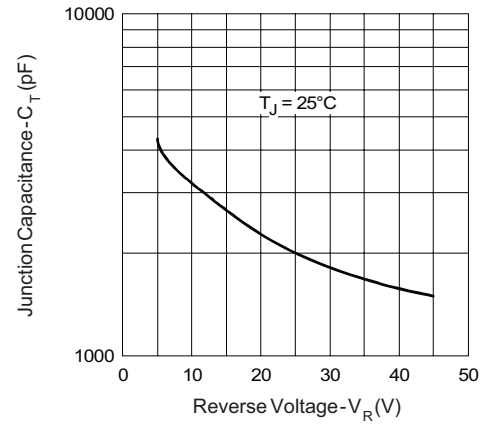


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

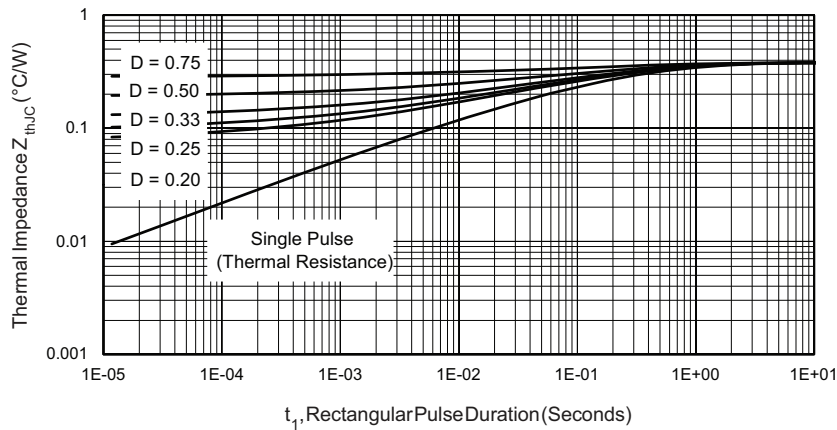


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

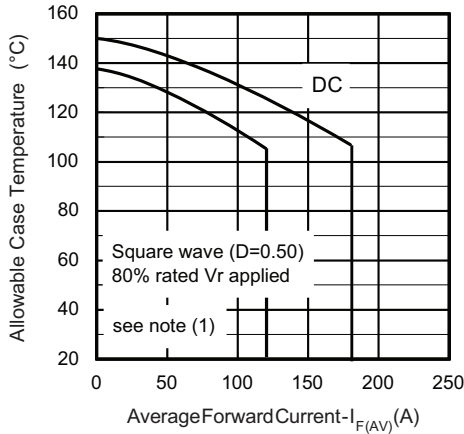


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

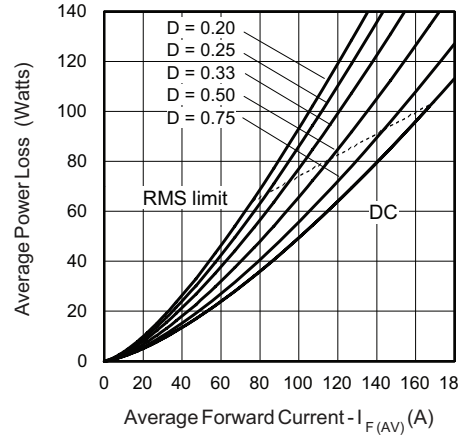


Fig. 6 - Forward Power Loss Characteristics

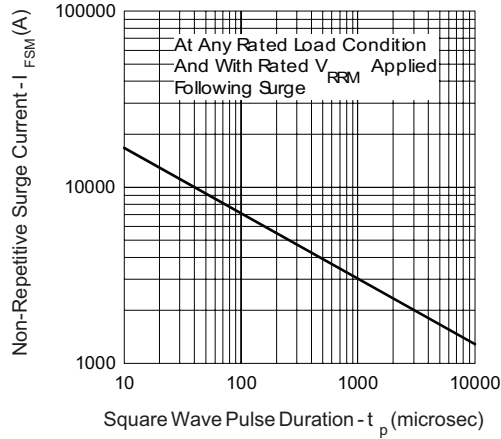


Fig. 7 - Maximum Non-Repetitive Surge Current

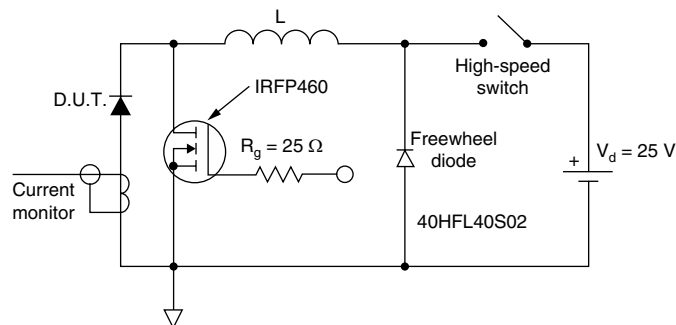


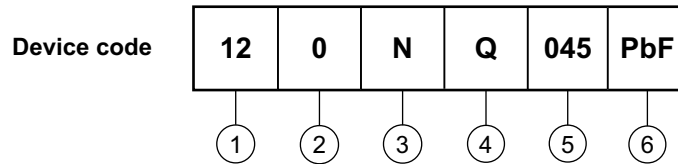
Fig. 8 - Unclamped Inductive Test Circuit

Note

- (9) Formula used: $T_C = T_J - (P_d + P_{d_{REV}}) \times R_{thJC}$;
 P_d = Forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6);
 $P_{d_{REV}}$ = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R



ORDERING INFORMATION TABLE



- 1** - Average current rating (x 10)
- 2** - Product silicon identification
- 3** - N = Not isolated
- 4** - Q = Schottky rectifier diode
- 5** - Voltage rating (045 = 45 V)
- 6** - Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95020



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